

Silicon Schottky Diode

LBAT60BT1

- High current rectifier Schottky diode with very low V_F drop (typ. 0.24 V at $I_F = 10\text{mA}$)
- For power supply applications
- For clamping and protection in low voltage applications
- For detection and step-up-conversion



Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Value | Unit |
|---|-----------|---------|------|
| Diode reverse voltage | V_R | 10 | V |
| Forward current | I_F | 3 | A |
| Surge forward current, ($t < 10\text{ms}$) | I_{FSM} | 5 | |
| Total power dissipation $T_s < 28^\circ\text{C}$ | P_{TOT} | 1350 | mW |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -55–150 | |

Driver Marking

LBAT60BT1=5

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

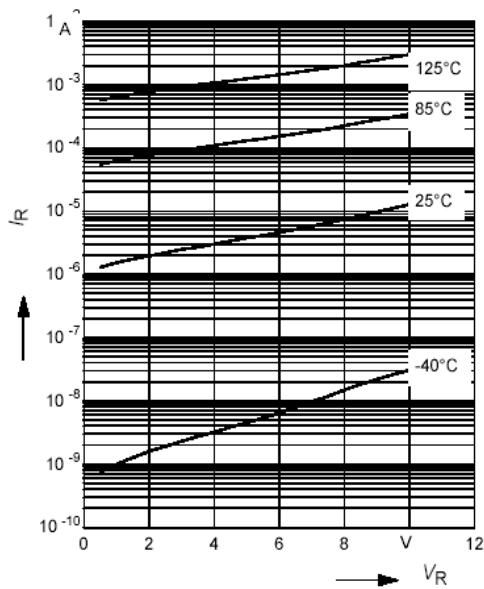
| Parameter | Symbol | Values | | | Unit |
|---|--------|--------|------|------|---------------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Reverse current | I_R | | | | μA |
| $V_R = 5 \text{ V}$ | | — | 5 | 15 | |
| $V_R = 8 \text{ V}$ | | — | 10 | 25 | |
| $V_R = 5 \text{ V}, T_A = 80^\circ\text{C}$ | | — | 100 | 800 | |
| $V_R = 8 \text{ V}, T_A = 80^\circ\text{C}$ | | — | 410 | 1500 | |
| Forward voltage | | | | | |
| $I_F = 10 \text{ mA}$ | V_F | | | | V |
| | | 0.2 | 0.24 | 0.3 | |
| $I_F = 100 \text{ mA}$ | | 0.26 | 0.32 | 0.38 | |
| $I_F = 500 \text{ mA}$ | | 0.32 | 0.4 | 0.5 | |
| $I_F = 1000 \text{ mA}$ | | 0.36 | 0.48 | 0.6 | |
| AC Characteristics | | | | | |
| Diode capacitance $V_R = 5 \text{ V}, f = 1 \text{ MHz}$ | C_T | 12 | 25 | 30 | pF |

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- Electrical characteristic curves

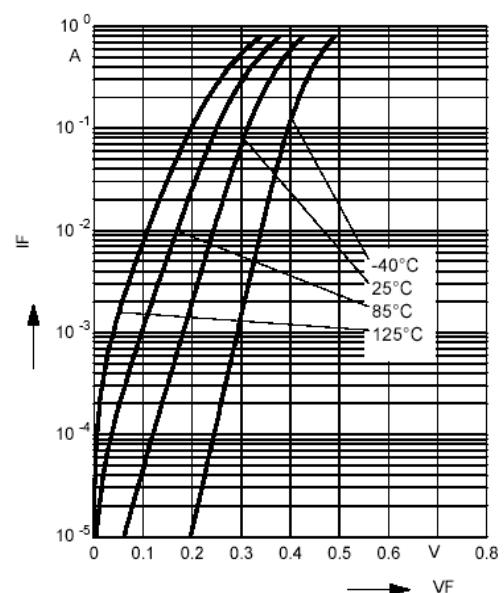
Reverse current $I_R = (V_R)$

T_A = Parameter

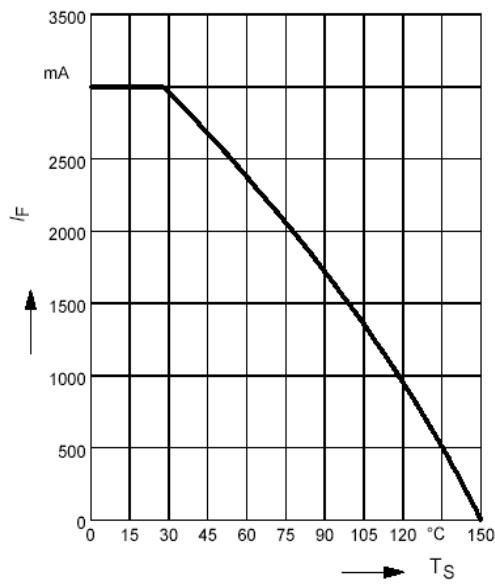


Forward current $I_F = (V_F)$

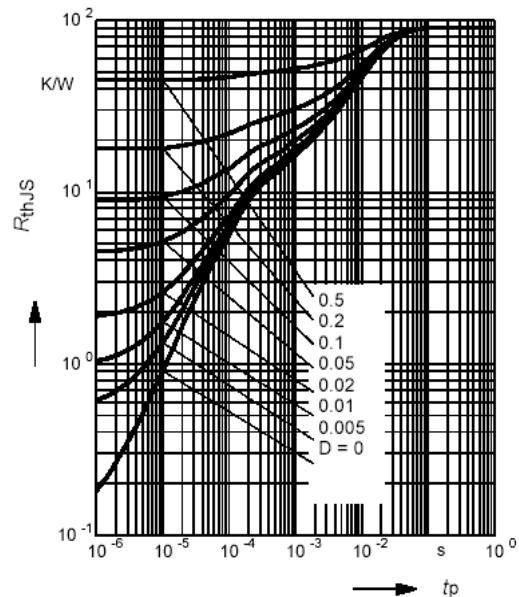
T_A = Parameter



Forward current $I_F = f(T_S)$

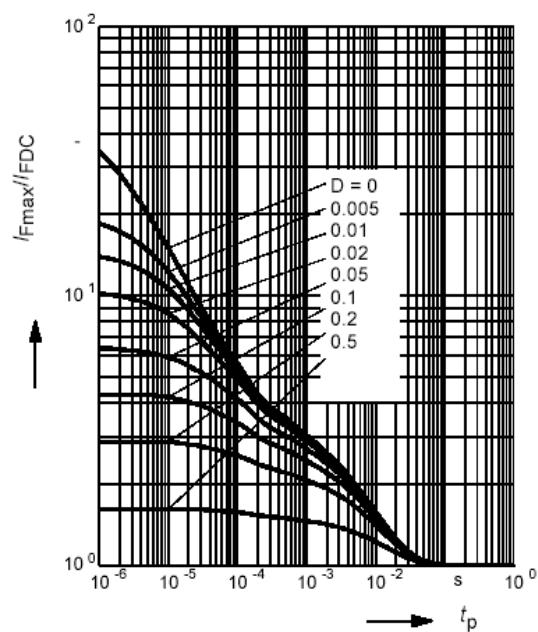


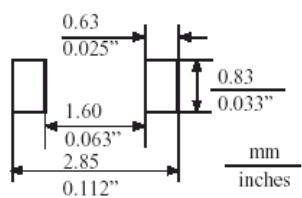
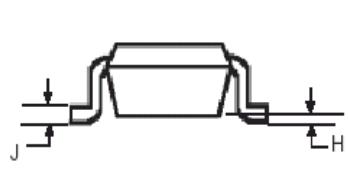
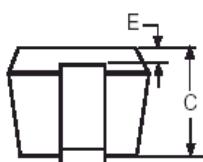
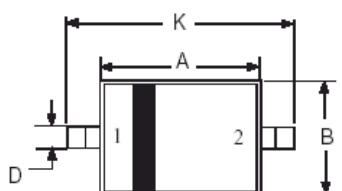
Permissible Puls Load $R_{thJS} = f(t_p)$



LBAT60BT1**Permissible Pulse Load**

$$I_{F\max}/I_{FDC} = f(t_p)$$



LBAT60BT1
SOD-323

NOTES:

1. CONTROLLING DIMENSION MILLIMETERS
2. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH
SOLDERPLATING

| DIN | MILLIMETERS | | INCHES | |
|-----|-------------|-------|-----------|--------|
| | MIN | MAX | MIN | MAX |
| A | 1.60 | 1.80 | 0.063 | 0.071 |
| B | 1.15 | 1.35 | 0.045 | 0.053 |
| C | 0.80 | 1.00 | 0.031 | 0.039 |
| D | 0.25 | 0.40 | 0.010 | 0.016 |
| E | 0.15 REF | | 0.006 REF | |
| H | 0.00 | 0.10 | 0.0000 | 0.004 |
| J | 0.089 | 0.177 | 0.0035 | 0.0070 |
| K | 2.30 | 2.7 | 0.091 | 0.106 |